

L Number	Hits	Search Text	DB	Time stamp
-	140	(aluminum or al) same (N or nitrogen) near4 (deposit\$4 or growth) and 117\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 15:32
-	10	(aluminum or al) near10 (promot\$4 or enhanc\$4 or improv\$5) same (N or nitrogen) near4 (deposit\$4 or growth) and 117\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 15:29
-	66	((aluminum or al) same (N or nitrogen) near4 (deposit\$4 or growth) and 117\$4.cccls.) and (MBE or molecular adj beam adj epitax\$)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 15:36
-	45	(N or nitrogen) near3 dop\$4 same (aluminum or al) near4 layer and 117\$5.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 16:00
-	53	(nitrogen) near3 dop\$4 same (aluminum or al) and 117\$5.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 16:02
-	33	(nitrogen) near3 dop\$4 same (aluminum or al) and 117/84-109.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 16:04
-	14	(nitrogen) near3 dop\$4 same (aluminum) and 117/84-109.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 16:07
-	5	(nitrogen) near3 dop\$4 same "iii-v" and 117/84-109.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/10 16:07
-	39	"iii-v" same (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 11:29
-	4	"iii-v" same (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) same monolayer and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 11:33
-	2	((algap or algan) same (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) or sequent\$4 near4 deposit\$4) and 117/\$4.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 11:34
-	17	(ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4).ti. and 117\$5.cccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 11:45
-	11	117\$5.cccls. and monolayer near6 deposit\$4 same (gallium or ga! and aluminum and nitrogen)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 11:45

-	36	(ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and 117\$5.ccls. and quantum near4 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 11:51
-	24	((ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and 117\$5.ccls. and quantum near4 well) and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 11:46
-	3	(ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) same (algainp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 13:08
-	6	(ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and nitrogen near4 dop\$4 and 117\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 13:12
-	4	algainnas same quantum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 15:54
-	9	algainnas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 15:57
-	10	(algaasn or algan or gaaln or gaalasn) same (gainas or gaasin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:02
-	25	"In-based" near5 "III-V"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:04
-	1	gainp same algainp same (hetero or hetero\$1structure) same nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:07
-	54	less near4 (atom\$3 near3 layer or monolayer) and 117\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:16
-	16	less near4 (atom\$3 near3 layer or monolayer) and 117\$4.ccls. and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:28
-	4	Mbe same (algan or gaaln) and 117\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:29
-	94	"iii-v" same (indium same aluminum same nitrogen or nitride) same ternary	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:47
-	6	"iii-v" same ternary same nitrogen near4 dop\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:48

-	65	"iii-v" same nitrogen near4 dop\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/11 17:19
-	115	(AlGaN or gallium near2 aluminum near3 nitride) same (gallium near3 indium) same (active or cladding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 09:43
-	17	(AlGaN or gallium near2 aluminum near3 nitride) same (gallium near3 indium) same well same thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 09:47
-	11	(AlGaN or gallium near2 aluminum near3 nitride) same (gallium near3 indium) same monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 09:49
-	23	(AlGaN or gallium near2 aluminum near3 nitride) same monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 10:04
-	1	(AlGaN or gallium adj aluminum adj nitride or GaAlN or gallium adj aluminum adj nitride) same (Gaalin or algain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 10:38
-	126	aluminum near4 gallium same mask\$3 and 257\$/5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 10:44
-	49	quantum near3 wire same "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:02
-	46	diffraction near4 grating same "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:06
-	9	algainnas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:35
-	5	(ingaas or gainas) same (algaasn or gaalasn)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:41
-	2	pseudo\$1mixed near4 crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:39
-	10	(ingaas or gainas) same monolayer and 117\$/5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:42
-	113	(ingaas or gainas) near4 superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:49

	2	(ingaas or gainas) near4 superlattice same aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 11:49
	2	ternary near4 superlattice same aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 13:23
	15	superlattice same "iii-v" same monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 13:39
	23	superlattice same "iii-v" same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 13:45
	6	superlattice same "iii-v" same (aluminum and indium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 13:55
	11	superlattice same "iii-v" same nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 13:55
	1	(aluminum near3 nitride or aln) same (indium near3 phosphide or inp) same superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 16:08
	2	(aluminum near3 nitride or al\$2n) same (indium near3 phosphide or in\$2p) same superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 16:09
	2	(aluminum near3 nitride or \$2al\$2n) same (indium near3 phosphide or \$2in\$2p) same superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 16:11
	14	(aluminum near3 nitride or al\$2n) same (indium near3 phosphide or inp) same monolayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 16:15
	98	(MBE or molecular adj beam adj epitax\$4 or CBE) same solid near4 source and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 17:02
	42	compound near2 semiconductor same "iii-v" same nitrogen near3 dop\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 17:04
	1	compound near2 semiconductor same "iii-v" same nitrogen near3 dop\$4 same superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 17:10
	3	"iii-v" same nitrogen near3 dop\$4 same superlattice	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 17:11

-	7	superlattice same (indium and aluminum and nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 17:29
-	7	nitrogen near3 dop\$4 same "iii-v" same aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/12 17:31
-	31	nitrogen near3 dop\$4 same aluminum near3 gallium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/13 13:47
-	21	algainp same mask\$4 same dop\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/13 17:08